

Fig. 1 is a cross-sectional view of a semiconductor device. The device includes a substrate 101. A top layer 102 is formed on the substrate 101. A central region 103 is defined within the top layer 102. This central region 103 contains a stack of layers 104, 105, 106, and 107. A side region 108 is defined adjacent to the central region 103. This side region 108 contains a stack of layers 109, 110, 111, and 113. A bottom layer 112 is located beneath the central region 103.

FIG. 2A
(PRIOR ART)

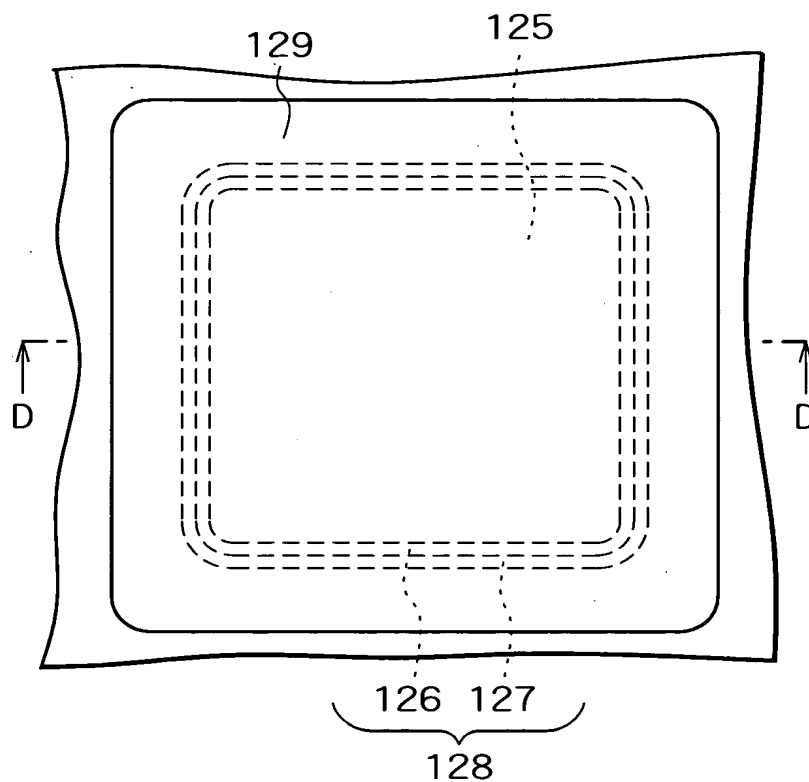


FIG. 2B (PRIOR ART)

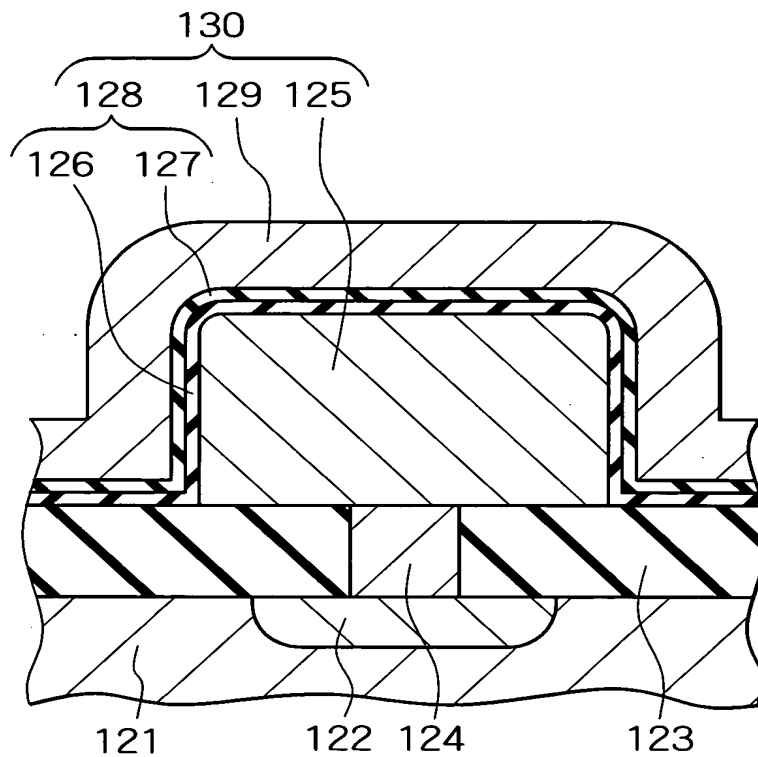


FIG. 3

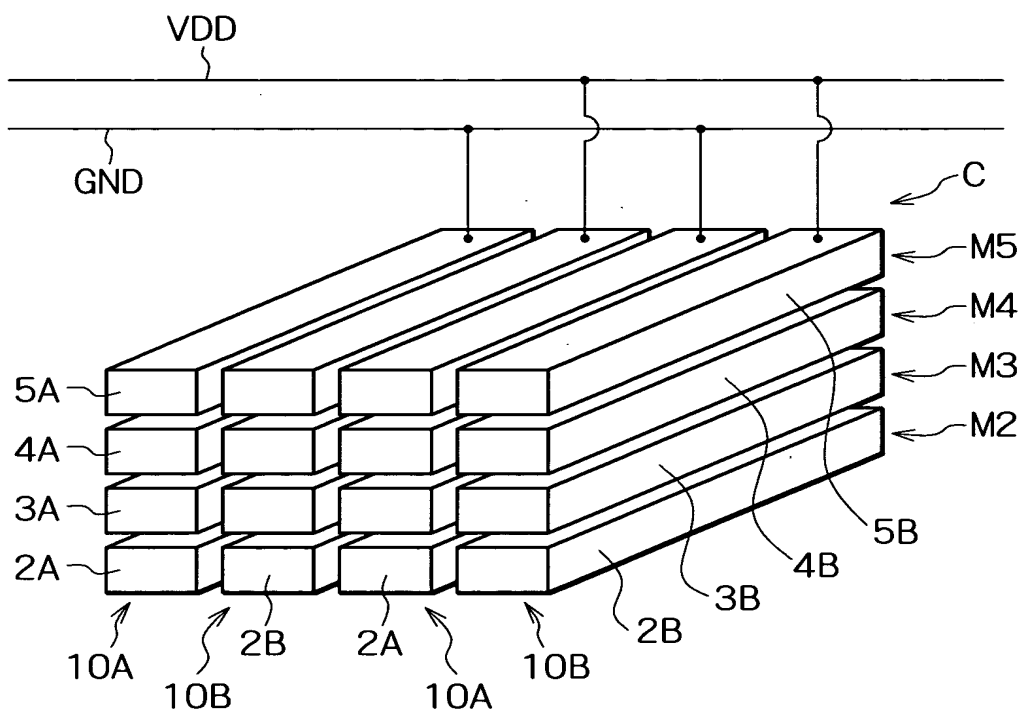


FIG. 4

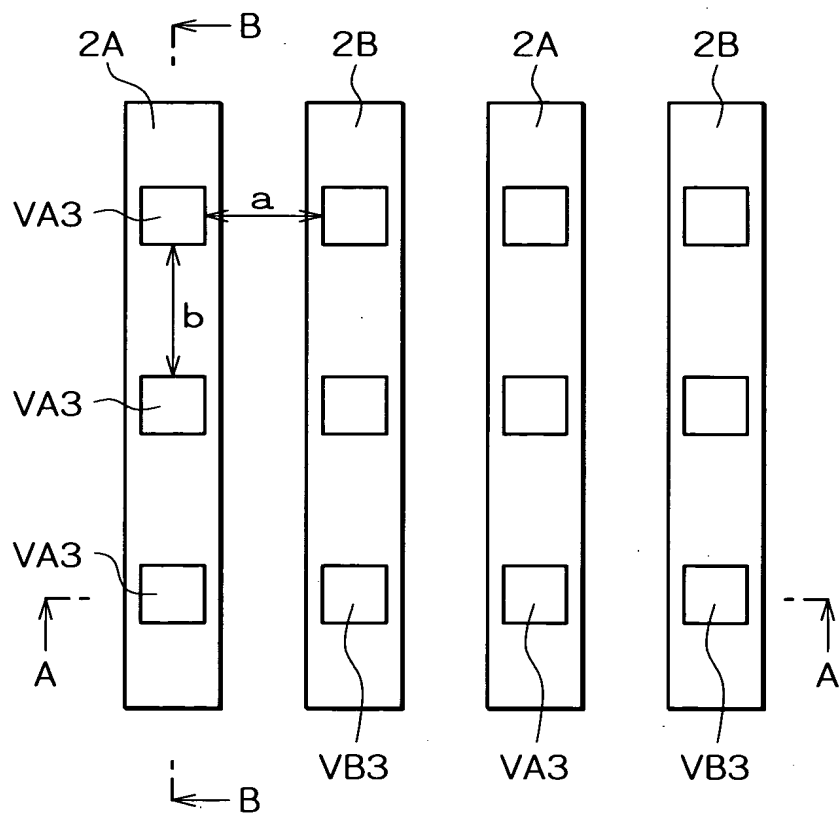


FIG. 5A

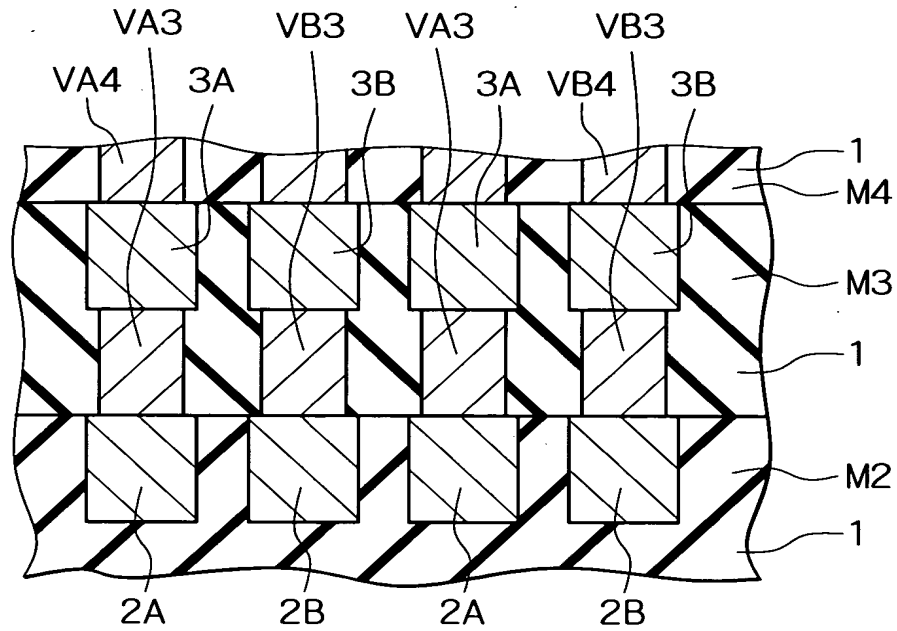


FIG. 5B

